

# Monolithic Dual Switching Diode

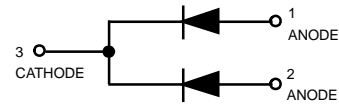
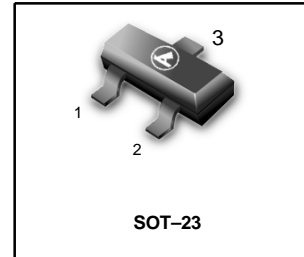
## Features

- We declare that the material of product compliance with RoHS requirements.

## Ordering Information

Device	Marking	Shipping
LBAV74LT1G	JA	3000/Tape&Reel
LBAV74LT3G	JA	10000/Tape&Reel

## LBAV74LT1G



## DEVICE MARKING

LBAV74LT1G = JA

## MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above $25^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above $25^\circ\text{C}$		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
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## OFF CHARACTERISTICS

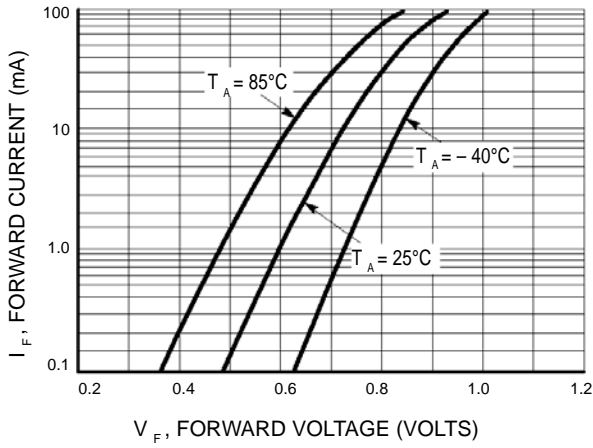
Reverse Breakdown Voltage ( $I_{(BR)} = 5.0 \mu\text{Adc}$ )	$V_{(BR)}$	50	—	Vdc
Reverse Voltage Leakage Current ( $V_R = 50 \text{ Vdc}$ , $T_J = 125^\circ\text{C}$ ) ( $V_R = 50 \text{ Vdc}$ )	$I_R$	—	100 0.1	$\mu\text{Adc}$
Diode Capacitance ( $V_R = 0$ , $f = 1.0 \text{ MHz}$ )	$C_D$	—	2.0	pF
Forward Voltage ( $I_F = 100 \text{ mAdc}$ )	$V_F$	—	1.0	Vdc
Reverse Recovery Time ( $I_F = 10 \text{ mAdc}$ , $I_{R(REC)} = 1.0 \text{ mAdc}$ , measured at $I_R = 1.0 \text{ mA}$ , $R_L = 100 \Omega$ )	$t_{rr}$	—	4.0	ns

1. FR-5 =  $1.0 \times 0.75 \times 0.062 \text{ in.}$

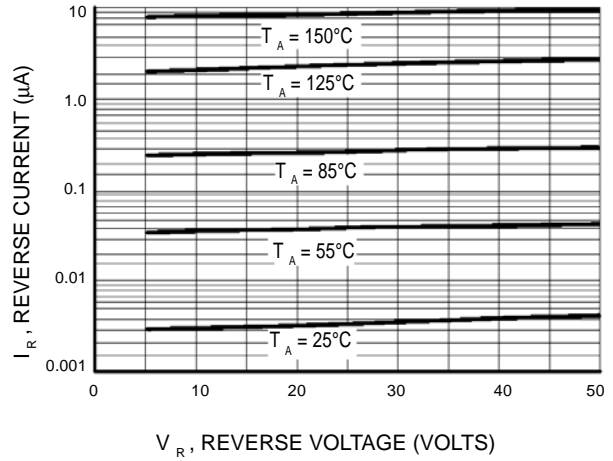
2. Alumina =  $0.4 \times 0.3 \times 0.024 \text{ in.}$  99.5% alumina.

**LBAV74LT1G**

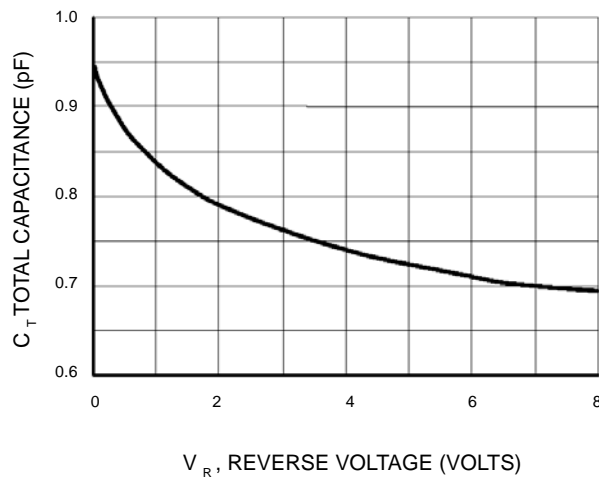
**Curves Applicable to Each Anode**



**Figure 1. Forward Voltage**

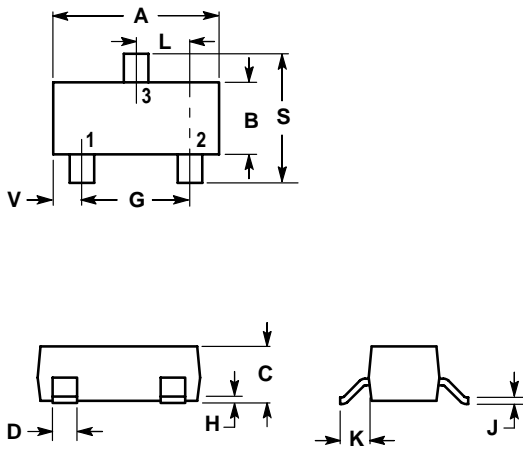


**Figure 3. Leakage Current**



**Figure 3. Capacitance**

SOT-23

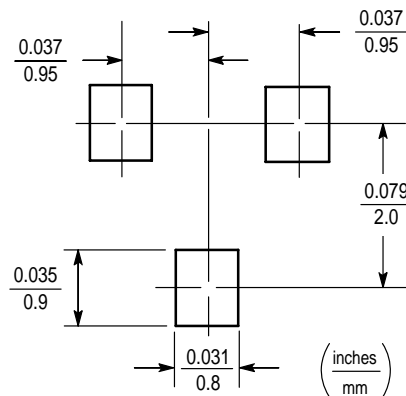


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. ANODE  
 2. NO CONNECTION  
 3. CATHODE



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